



2SA816 · 2SC1626

捷多邦, 专业PCB打样工厂, 24小时加急出货

PNP · NPN SILICON PLANAR EPITAXIAL POWER TRANSISTORS

MICRO ELECTRONICS

CASE TO-220B

THE 2SA816 (PNP) AND 2SC1626 (NPN) ARE SILICON PLANAR EPITAXIAL COMPLEMENTARY PAIR SPECIALLY DESIGNED FOR THE DRIVER STAGES OF 30-50W HI-FI AMPLIFIERS. THEY ARE ALSO SUITABLE FOR MEDIUM SPEED SWITCHING UP TO 2A PEAK CURRENT.



BCE

ABSOLUTE MAXIMUM RATINGS

For p-n-p devices, voltage and current values are negative.

Collector-Base Voltage	V _{CBO}	80V
Collector-Emitter Voltage	V _{CEO}	80V
Emitter-Base Voltage	V _{EBO}	5V
Collector Current	I _C	750mA
Collector Peak Current (t ≤ 10ms)	I _{CM}	2A
Total Power Dissipation @ T _C ≤ 25°C	P _{tot}	10W
@ T _A ≤ 25°C		1.5W
Junction Temperature	T _j	150°C
Storage Temperature Range	T _{stg}	-55 to +150°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BV _{CBO}	80			V	I _C =0.1mA I _B =0
Collector-Emitter Breakdown Voltage	LV _{CEO} *	80			V	I _C =10mA I _B =0
Collector Cutoff Current	I _{CBO}			0.5	μA	V _{CB} =30V I _E =0
Emitter Cutoff Current	I _{EBO}			1	μA	V _{EB} =5V I _C =0
Collector-Emitter Saturation Voltage	V _{CE(sat)} *			0.5	V	I _C =500mA I _B =50mA
Base-Emitter Voltage	V _{BE} *			1	V	I _C =500mA V _{CE} =2V
D.C. Current Gain (Note)	H _{FE 1} *	70		240		I _C =150mA V _{CE} =2V
	H _{FE 2} *	40				I _C =500mA V _{CE} =2V
Current Gain-Bandwidth Product	f _T	50	100		MHz	I _C =150mA V _{CE} =2V
Collector-Base Capacitance 2SA816	C _{ob}		20		pF	V _{CB} =10V I _E =0
2SC1626			13		pF	f=1MHz

*Pulse Test : Pulse Width=0.3ms, Duty Cycle=1%

note : H_{FE 1} is classified as follows. Group O : 70-140, Group Y : 120-240

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1-2-BMP



TYPICAL CHARACTERISTICS

($T_A=25^\circ\text{C}$ unless otherwise noted)

